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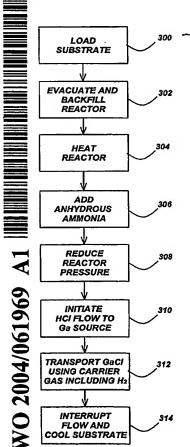
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(54) Title: GROWTH OF PLANAR, NON-POLAR A-PLANE GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY



(57) Abstract: Highly planar non-polar a-plane GaN films are grown by hydride vapor phase epitaxy (HVPE). The resulting films are suitable for subsequent device regrowth by a variety of growth techniques

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